

# 1 Well

 <p>Si (p-type)</p>	We start with a p-type silicon wafer
 <p>SiO2 Si (p-type)</p>	We grow an oxide layer of approximately 1000 angstrom thickness (see documentation)
 <p>Resist SiO2 Si (p-type)</p>	We thin film deposit a layer of resist
 <p>SiO2 Si (p-type)</p>	We expose and develop the pattern from the GDS2 layer information
 <p>Si (p-type)</p>	We etch the 1000 angstrom oxide layer
 <p>N Si (p-type)</p>	Ion implantation: Implant Phosphorus (P); n-type impurity to create N-well
 <p>N Si (p-type)</p>	Remove resist
 <p>N Si (p-type)</p>	Remove oxide